

# N-Channel 25-V (D-S) MOSFET

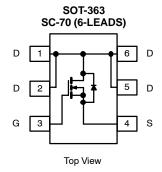
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)		
25	0.35 @ V <sub>GS</sub> = 4.5 V	1.57	1.3		
	0.45 @ V <sub>GS</sub> = 2.5 V	1.39	1.5		

#### **FEATURES**

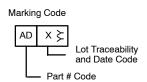
• Thermally Enhanced SC-70 Package

#### **APPLICATIONS**

• Load Switch for Portable Devices



Ordering Information: Si1404DH-T1 Si1404DH-T1—E3 (Lead (Pb)-Free)



<b>ABSOLUTE MAXIMUM RATINGS</b>	(T <sub>A</sub> = 25°C UN	LESS OTHE	ERWISE NO	TED)		
Parameter		Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	25		٧	
Gate-Source Voltage		V <sub>GS</sub>	±8			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	T <sub>A</sub> = 25°C	I <sub>D</sub>	1.57	1.30		
Continuous Drain Current (1) = 150 C)-	T <sub>A</sub> = 85°C		1.13	0.93	Α	
Pulsed Drain Current		I <sub>DM</sub>	4		^	
Continuous Diode Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.23	0.83		
Manifestor Device Discipations	T <sub>A</sub> = 25°C		1.47	1.0	10/	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85°C	- P <sub>D</sub>	0.76	0.52	W	
Operating Junction and Storage Temperature Range	<u>.</u>	T <sub>J</sub> , T <sub>stg</sub>	-55	5 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 5 sec	$R_{thJA}$	70	85	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		100	125		
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	44	55		

Notes a. Surface Mounted on 1" x 1" FR4 Board.



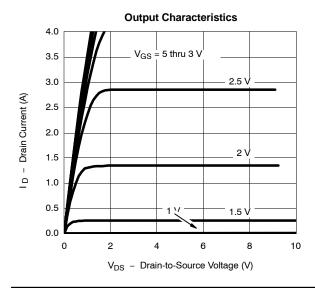
SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit	
Static			•			•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.6		1.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±8 V			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$I_{DSS}$ $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85^{\circ}\text{C}$			1 5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	4.0			Α	
D : 0	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 1.57 \text{ A}$		0.280	0.35		
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 2.5 \text{ V}, I_D = 1.39 \text{ A}$		0.355	0.45	Ω	
Forward Transconductancea	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 0.75 A		1.5		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_S = 1.23 \text{ A}, V_{GS} = 0 \text{ V}$		0.85	1.2	V	
Dynamic <sup>b</sup>	·						
Total Gate Charge	Qg			1.3	2.8	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, \ V_{GS} = 4.5 \text{ V}, \ I_D = 1.57 \text{ A}$		0.31			
Gate-Drain Charge	$Q_{gd}$			0.49			
Turn-On Delay Time	t <sub>d(on)</sub>			11	20		
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_1 = 20 \Omega$		18	30	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD}$ = 15 V, $R_L$ = 20 $\Omega$ $I_D \cong 0.75$ A, $V_{GEN}$ = 4.5 V, $R_g$ = 6 $\Omega$		17	30		
Fall Time	t <sub>f</sub>			11	20	1	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.23 A, di/dt = 100 A/μs		30	60		

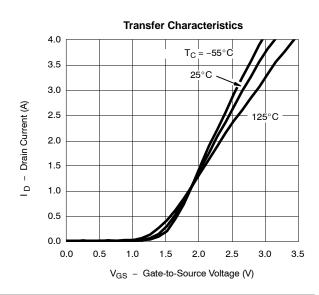
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



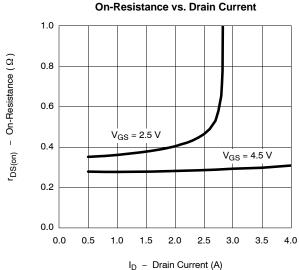


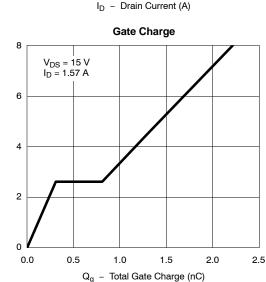


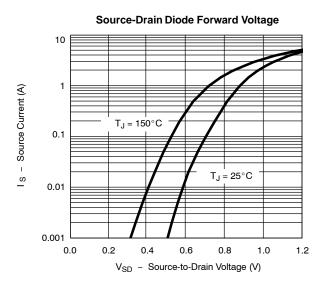
V <sub>GS</sub> - Gate-to-Source Voltage (V)

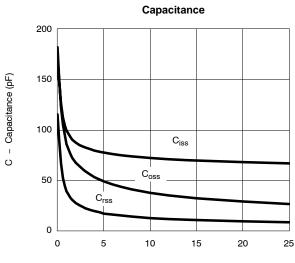
## **Vishay Siliconix**

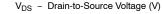
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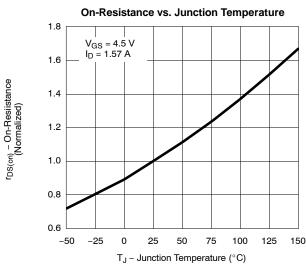


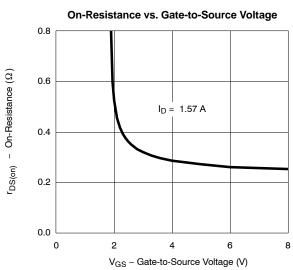






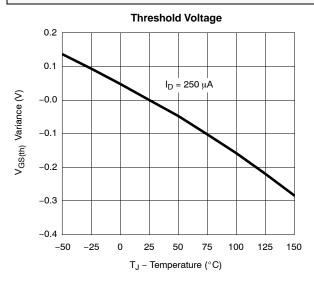


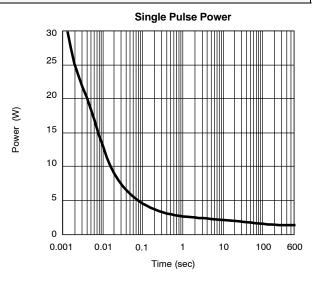


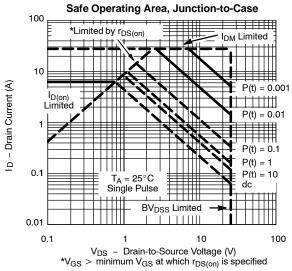


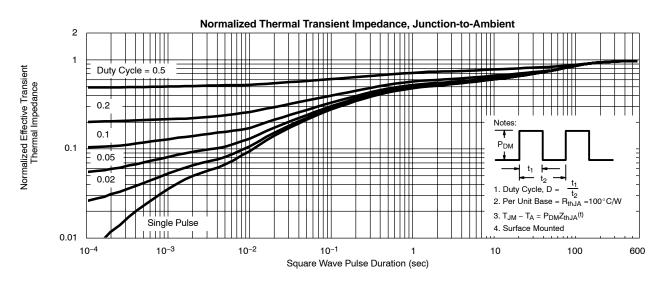


## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)











## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

#### Normalized Thermal Transient Impedance, Junction-to-Foot 2 Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5 0.2 0.1 0.05 0.02 Single Pulse 0.01 10-4 10-3 10-2 10-1 1 10 Square Wave Pulse Duration (sec)

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